## NSN 5962-01-352-1009

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Body Length:
0.540 inches
Body Width:
Between 0.245 inches and 0.300 inches
Body Height:
Between 0.045 inches and 0.100 inches
Maximum Power Dissipation Rating:
303.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
5895-01-299-3419 converter, signal data
Features Provided:
Hermetically sealed and burn in and monolithic and positive outputs
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
F-9 mil-m-38510
Current Rating Per Characteristic:
55.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or-invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
50.00 nanoseconds delay
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)
Terminal Type And Quantity:

20 flat leads

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Shelf Life:

N/a

**Unit Of Measure:** 

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Demilitarization:

Yes - demil/mli

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